

IN THE CLAIMS

1. (Currently amended) A metallization structure in a multilayer stack comprising a dielectric layer and one or more surrounding dielectric layers situated above or below the dielectric layer, a dielectric constant of the dielectric layer being greater than a dielectric constant of the surrounding dielectric layers, and a metallization structure which is arranged on the dielectric layer and is arranged at a distance from a ground electrode, characterized in that wherein the metallization structure has a capacitor electrode (22) and a line (24) that acts as a coil, where the capacitor electrode (22) and the line (24) are arranged in a common plane which lies parallel to the ground electrode (30) at a distance h_1 , and in that wherein $w/h_1 > 3$, where w is the width of the line (24).
2. A metallization structure as claimed in claim 1, characterized in that wherein a second ground electrode (32) is provided, the plane comprising capacitor electrode (22) and line (24) being arranged parallel to said second ground electrode at a distance h_2 , and in that the plane comprising capacitor electrode (22) and line (24) lies between the first and second ground electrodes (30, 32), where $w/h_2 > 3$.
3. (Canceled)
4. (Canceled)
5. (Currently amended) A multilayer stack as claimed in claim 23, characterized in that wherein the following applies in respect of the layer thickness (d_{medium}) of the

dielectric layer (14):

$$\frac{\epsilon_{\text{medium}} \cdot d_{\epsilon}}{\epsilon \cdot d_{\text{medium}}} > 5$$

wherein the dielectric constant of and a thickness of the dielectric layer are ϵ_{medium} and d_{medium} , respectively, and the dielectric constant of and a thickness of the surrounding dielectric layers are ϵ and d_{ϵ} , respectively.

6. (Currently amended) A multilayer stack as claimed in claim 3 comprising one or more additional metallization structures in the plane, characterized in that wherein

$$\frac{\epsilon_{\text{medium}} \cdot d_{\text{min}}}{\epsilon \cdot d_{\text{medium}}} > 7 ,$$

where d_{min} is the minimum distance to the next nearest metallization structure in the plane.

7. (Currently amended) A multilayer stack as claimed in claim 3, characterized in that wherein it the multilayer stack comprises magnetic layers.

8. (Currently amended) A multilayer stack as claimed in claim 23, produced in a multilayer laminate process.

9. (Currently amended) A multilayer stack as claimed in claim 23, produced in an LTCC process.

10. (Canceled)